

# **Description**

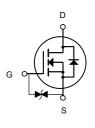
The DMN2025U-7 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

# D S S S S SOT-23

### **General Features**

 $V_{DS}$  = 20V  $I_D$  =6A  $R_{DS(ON)}$  < 17m $\Omega$  @  $V_{GS}$ =4. 5V

ESD=2500V HBM



N-Channel MOSFET

## **Application**

Battery protection
Load switch
Uninterruptible power supply

# **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
DMN2025U-7	SOT-23	HXY MOSFET	3000

# Absolute Maximum Ratings (T<sub>A</sub>=25 <sup>°</sup>C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>G</sub> s	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous	6	Α
Ідм	Drain Current-Pulsed (Note 1)	30	Α
P <sub>D</sub>	Maximum Power Dissipation	1.4	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	89	°C/W



# Electrical Characteristics (T<sub>A</sub>=25°Cunless otherwise noted)

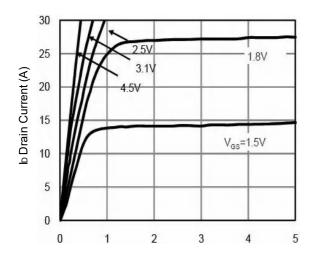
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	20		-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	$V_{GS}$ =±10 $V$ , $V_{DS}$ =0 $V$	-	-	±10	μA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.45	0.7	1.0	V
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6.5A	-	14	17	mΩ
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.5A	-	18	23	mΩ
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =5A	-	28	40	mΩ
Forward Transconductance	grs	V <sub>DS</sub> =5V,I <sub>D</sub> =6.5A	8	-	-	S
Input Capacitance	C <sub>lss</sub>		-	660	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,	-	160	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	87	-	PF
Turn-on Delay Time	t <sub>d(on)</sub>		-	0.5		nS
Turn-on Rise Time	tr	V <sub>DD</sub> =10V,R <sub>L</sub> =1. 5Ω	-	1		nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}=5V,R_{GEN}=3\Omega$	-	12		nS
Turn-Off Fall Time	t <sub>f</sub>		-	4		nS
Total Gate Charge	Qg		-	8		nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =10V,I <sub>D</sub> =6.5A,	-	2.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =4.5V	-	3	-	nC
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V,I <sub>S</sub> =6.5A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	6.0	Α

### Notes:

Repetitive Rating: Pulse width limited by maximum junction temperature. Surface Mounted on FR4 Board,  $t \leq 10$  sec. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ . Guaranteed by design, not subject to production



### **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

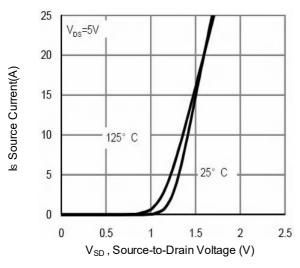


Fig.3 Forward Characteristics of Reverse

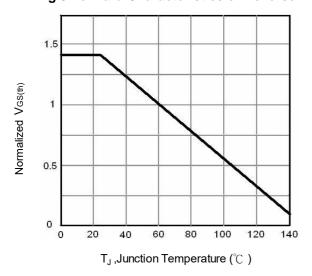


Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$ 

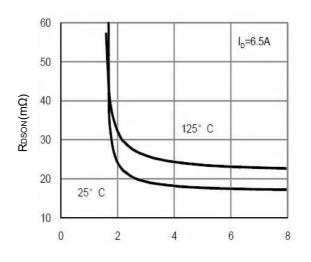


Fig.2 On-Resistance vs. Gate-Source

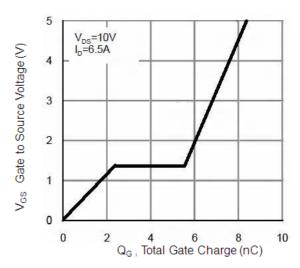


Fig.4 Gate-Charge Characteristics

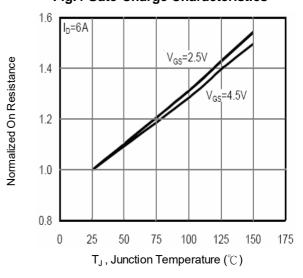
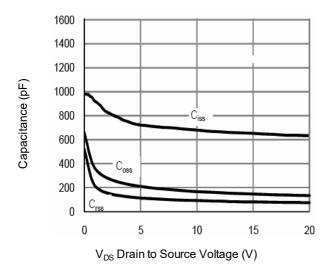


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>





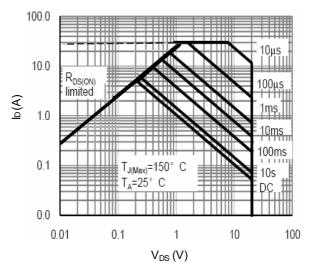
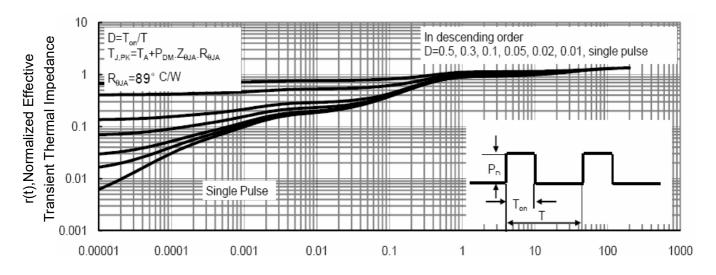
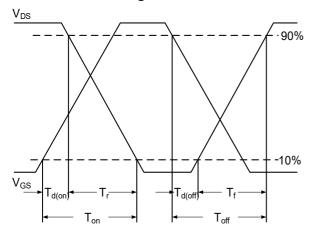


Fig.7 Capacitance

Fig.8 Safe Operating Area



Square Wave Pluse Duration(sec)
Fig.9 Normalized Maximum Transient Thermal Impedance





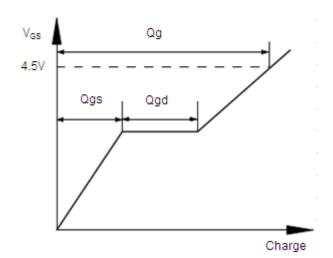
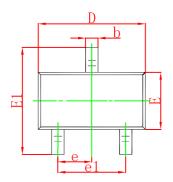
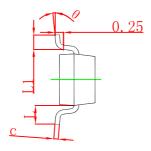


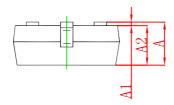
Fig.11 Gate Charge Waveform



# **SOT-23 Package Outline Dimensions**

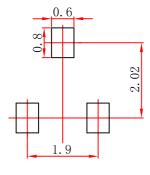






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

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